

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

## SS32B-MS TRHU SS3200B-MS

Product specification


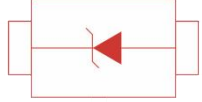
## Features

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- High forward surge current capability
- High temperature soldering guaranteed:
- 250°C/10 seconds, 0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension


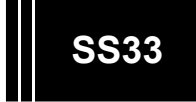
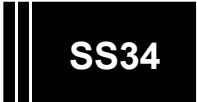
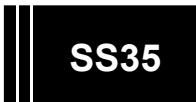



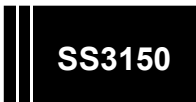
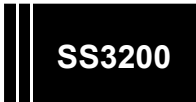
## MECHANICAL DATA

- Case : JEDEC DO-214AA/SMB molded plastic body
- Terminals : Solderable per MIL-STD-750, Method 2026
- Polarity : Color band denotes cathode end Mounting
- Position : Any
- Weight : 0.003 ounce, 0.095 grams

## Reference News

DO-214AA/SMB	Schematic Diagram
	

## Marking

SS32B-MS	SS33B-MS	SS34B-MS	SS35B-MS	SS36B-MS
				
SS38B-MS	SS310B-MS	SS3150B-MS	SS3200B-MS	
				

## Maximum Ratings And Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	SYMBOLS	SS32B -MS	SS33B -MS	SS34B -MS	SS35B -MS	SS36B -MS	SS38B -MS	SS310B -MS	SS3150B -MS	SS3200B -MS	UNITS
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	20	30	40	50	60	80	100	150	200	V
Maximum RMS voltage	V <sub>RMS</sub>	14	21	28	35	42	56	70	105	140	V
Maximum DC blocking voltage	V <sub>DC</sub>	20	30	40	50	60	80	100	150	200	V
Maximum average forward rectified current	I <sub>AV</sub>	3									A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	80									A
Maximum instantaneous forward voltage at 3.0A	V <sub>F</sub>	0.55			0.7		0.85		0.95		V
Maximum DC reverse current     T <sub>A</sub> =25℃ at rated DC blocking voltage     T <sub>A</sub> =100℃	I <sub>R</sub>	0.5 5					0.3 3				mA
Typical junction capacitance (NOTE 1)	C <sub>J</sub>	450			400						pF
Typical thermal resistance (NOTE 2)	R <sub>θJA</sub>	60									℃/W
Operating junction temperature range	T <sub>J</sub>	-55 to +150									℃
Storage temperature range	T <sub>STG</sub>	-55 to +150									℃

**Note:** 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.  
2. P.C.B. mounted with 2.0"x2.0" (5.0x5.0cm) copper pad areas

## Typical Characteristics

Fig.1 Forward Current Derating Curve

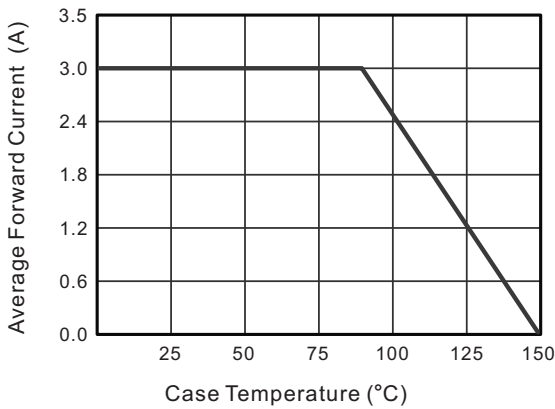


Fig.2 Typical Reverse Characteristics

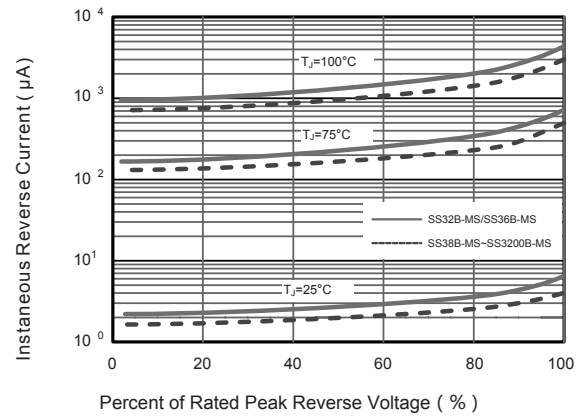


Fig.3 Typical Forward Characteristic

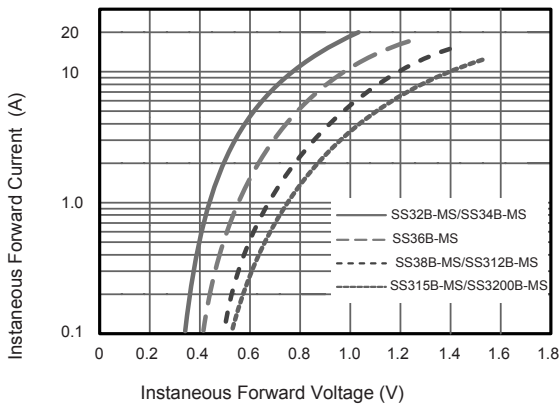


Fig.4 Typical Junction Capacitance

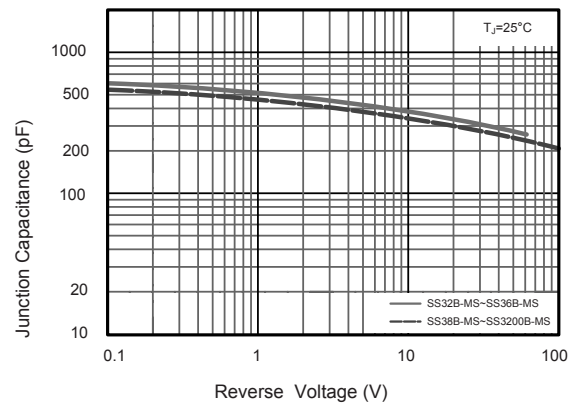


Fig.5 Maximum Non-Repertive Peak Forward Surge Current

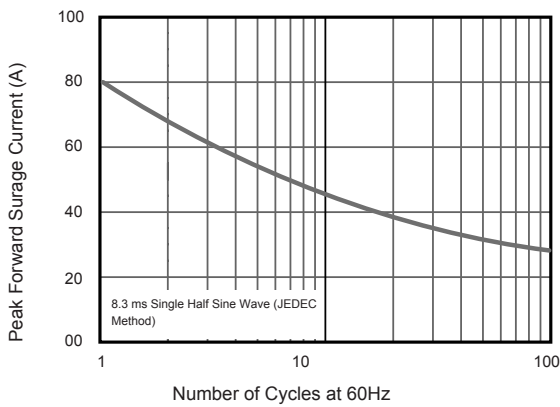
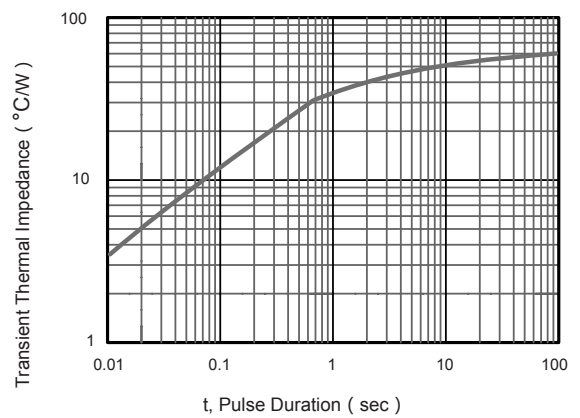
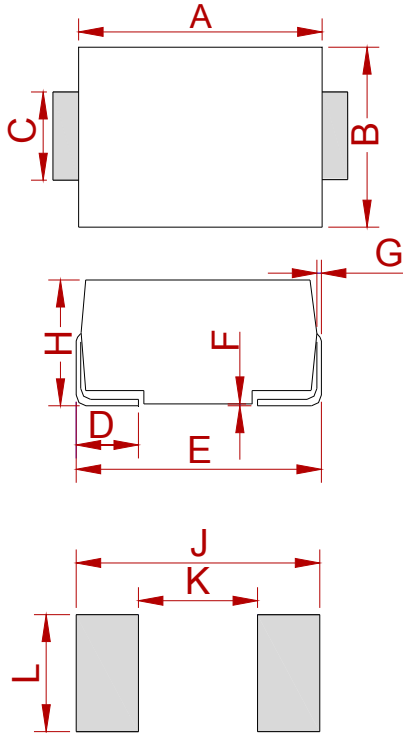


Fig.6- Typical Transient Thermal Impedance



## PACKAGE MECHANICAL DATA



DO-214AA (SMB)

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.25	4.75	0.167	0.187
B	3.30	3.94	0.130	0.155
C	1.85	2.21	0.073	0.087
D	0.76	1.52	0.030	0.060
E	5.08	5.59	0.200	0.220
F	0.051	0.203	0.002	0.008
G	0.15	0.31	0.006	0.012
H	2.11	2.44	0.083	0.096
J	6.80		0.270	
K		2.60		0.100
L	2.40		0.090	

## REEL SPECIFICATION

P/N	PKG	QTY
SS32B-MS TRHU SS3200B-MS	DO-214AA(SMB)	3000

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